

## Schottky barrier diode

## RB751S-40 / RB751V-40

## ●Applications

High speed switching  
For Detection

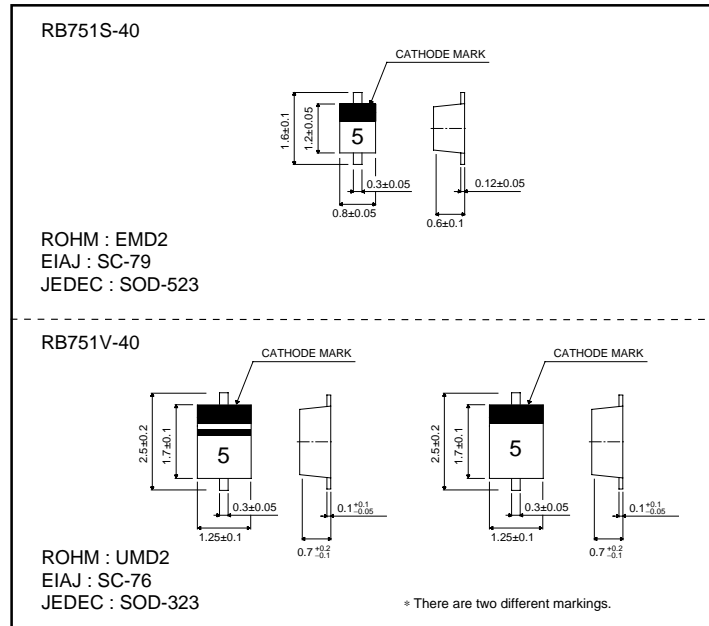
## ●Features

- 1) Small surface mounting type.  
(EMD2, UMD2)
- 2) Low reverse current and low forward voltage.
- 3) High reliability.

## ●Construction

Silicon epitaxial planar

## ●External dimensions (Units : mm)



## ●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	$V_{RM}$	40	V
DC reverse voltage	$V_R$	30	V
Mean rectifying current	$I_o$	30	mA
Peak forward surge current*	$I_{FSM}$	200	mA
Junction temperature	$T_j$	125	°C
Storage temperature	$T_{stg}$	-40~+125	°C

\* 60 Hz for 1  $\mu$ s

## ●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_F$	-	-	0.37	V	$I_F = 1\text{mA}$
Reverse current	$I_R$	-	-	0.5	$\mu\text{A}$	$V_R = 30\text{V}$
Capacitance between terminals	$C_T$	-	2.0	-	pF	$V_R = 1\text{V}, f = 1\text{MHz}$

Note) ESD sensitive product handling required.

Diodes

● Electrical characteristic curves (Ta = 25°C)

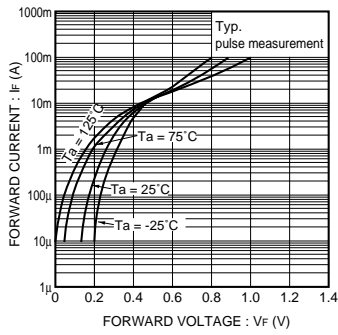


Fig. 1 Forward characteristics

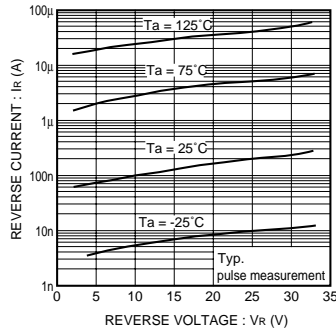


Fig. 2 Reverse characteristics

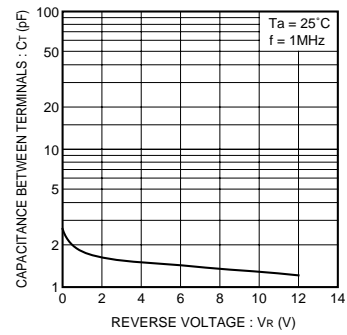


Fig. 3 Capacitance between terminals characteristics